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Term	Documents
SEMICONDUCTOR.USPT,PGPB.	237818
SEMICONDUCTORS.USPT,PGPB.	29523
SION.USPT,PGPB.	6335
SIONS.USPT,PGPB.	199
SILICON.USPT,PGPB.	271943
SILICONS.USPT,PGPB.	882
OXYNITRIDE.USPT,PGPB.	5462
OXYNITRIDES.USPT,PGPB.	852
ARC.USPT,PGPB.	164653
ARCS.USPT,PGPB.	24520
((SEMICONDUCTOR) AND ((SION OR (SILICON OXYNITRIDE)) SAME (ARC OR DARC OR ANTIREFLECT\$3 OR (ANTI-REFLECT\$3) OR (AR (COAT\$3 OR FILM OR LAYER))) SAME (REFRACTIVE INDEX) SAME (EXTINCTION COEFFICIENT))).USPT,PGPB.	8

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Database:**Refine Search:**

(semiconductor) and ((SiON or (silicon
oxynitride)) same (ARC or DARC or
antireflect\$3 or (anti-reflect\$3) or (AR

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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
USPT,PGPB	(semiconductor) and ((SiON or (silicon oxynitride)) same (ARC or DARC or antireflect\$3 or (anti-reflect\$3) or (AR (coat\$3 or film or layer))) same (refractive index) same (extinction coefficient))	8	<u>L39</u>
USPT,PGPB	(SiON or (silicon oxynitride)) same (treat\$4) same (oxygen or O2 or "O.sub.2") same (nitrogen or N2 or "N.sub.2") same (mixture or combination)	9	<u>L38</u>
JPAB,EPAB,DWPI,TDBD	(SiON or (silicon oxynitride)) and (anneal\$3) and (oxygen or O2 or "O.sub.2") and (nitrogen or N2 or "N.sub.2") and (mixture or combination)	1	<u>L37</u>
USPT,PGPB	(SiON or (silicon oxynitride)) same (anneal\$3) same (oxygen or O2 or "O.sub.2") same (nitrogen or N2 or "N.sub.2") same (mixture or combination)	7	<u>L36</u>
USPT,PGPB	(Vanguard International Semiconductor)	544	<u>L35</u>
USPT,PGPB	(Taiwan semiconductor)	1713	<u>L34</u>
USPT,PGPB	(Taiwan semiconductor) and (Vanguard International Semiconductor)	0	<u>L33</u>
USPT,PGPB	(antireflect\$3 or (anti-reflect\$3) or DARC or ARC or (AR (coat\$3 or film or layer))) same (SiON or (silicon oxynitride) or "SiON") same (polysilicon or SiN or (silicon nitride)) same photoresist	82	<u>L32</u>
USPT,PGPB	(antireflect\$3 or (anti-reflect\$3) or DARC or ARC or (AR (coat\$3 or film or layer))) same (SiON or (silicon oxynitride) or "SiON") same (polysilicon or SiN or (silicon nitride))	276	<u>L31</u>
JPAB,EPAB,DWPI,TDBD	((antireflect\$3 or (anti-reflect\$3) or DARC or ARC or (AR (coat\$3 or film or layer))) and (anneal\$3 or (heat treat\$4))) and ((alter\$3 or modify\$3 or chang\$3 or adjust\$3) with ((optical propert\$3) or (extinction coefficient) or (refractive index)))	5	<u>L30</u>
USPT,PGPB	((antireflect\$3 or (anti-reflect\$3) or DARC or ARC or (AR (coat\$3 or film or layer))) same (anneal\$3 or (heat treat\$4))) same ((alter\$3 or modify\$3 or chang\$3 or adjust\$3) with ((optical propert\$3) or (extinction coefficient) or (refractive index)))	19	<u>L29</u>
USPT,PGPB	(Micron Technology) and ((antireflect\$3 or (anti-reflect\$3) or DARC or ARC or (AR (coat\$3 or film or layer))) same (anneal\$3 or (heat treat\$4)))	20	<u>L28</u>
USPT,PGPB	6274292	2	<u>L27</u>
USPT,PGPB	L25 and ((anneal\$3 or (heat treat\$4)) with (N2 or O2 or "N.sub.2" or "O.sub.2" or oxygen or nitrogen))	5	<u>L26</u>

USPT,PGPB	(extinction coefficient) same ((heat treat\$4) or anneal\$3)	39	<u>L25</u>
JPAB,EPAB,DWPI,TDBD	(extinction coefficient) and ((heat treat\$4) or anneal\$3)	13	<u>L24</u>
USPT,PGPB	(extinction coefficient) with ((heat treat\$4) or anneal\$3)	15	<u>L23</u>
USPT,PGPB	L18 and (extinction coefficient)	12	<u>L22</u>
JPAB,EPAB,DWPI,TDBD	(semiconductor) and (SiN or (silicon nitride) or ("SiN.sub.X") or polysilicon) and ((ARC or DARC or (antireflect\$3) or (anti-reflect\$3) or (antireflect\$3) or SiON or (silicon oxynitride) or "SiON" or SiONH or "SiONH") and ((heat treat\$3) or anneal\$3) and (O2 or N2 or oxygen or nitrogen or "O.sub.2" or "N.sub.2"))	15	<u>L21</u>
USPT,PGPB	L19 and (DARC or ARC or (antireflect\$3) or (anti-reflect\$3) or (antireflect\$3) or (AR (coat\$3 or film or layer)))	77	<u>L20</u>
USPT,PGPB	(semiconductor) and (SiN or (silicon nitride) or ("SiN.sub.X") or polysilicon) and ((ARC or DARC or (antireflect\$3) or (anti-reflect\$3) or (antireflect\$3) or SiON or (silicon oxynitride) or "SiON" or SiONH or "SiONH") same ((heat treat\$3) or anneal\$3) same (O2 or N2 or oxygen or nitrogen or "O.sub.2" or "N.sub.2"))	185	<u>L19</u>
USPT,PGPB	(semiconductor) and (SiN or (silicon nitride) or ("SiN.sub.X") or polysilicon) and ((AR or ARC or DARC or (antireflect\$3) or (anti-reflect\$3) or (antireflect\$3) or SiON or (silicon oxynitride) or "SiON" or SiONH or "SiONH") same ((heat treat\$3) or anneal\$3))	948	<u>L18</u>
USPT,PGPB	(DARC) and ((AR or (antireflect\$3) or (anti-reflect\$3) or (antireflect\$3) or SiON or (silicon oxynitride) or "SiON") same ((heat treat\$3) or anneal\$3))	3	<u>L17</u>
USPT,PGPB	(DARC) and ((DARC or SiON or (silicon oxynitride) or "SiON") same ((heat treat\$3) or anneal\$3))	3	<u>L16</u>
USPT,PGPB	(DARC) and ((DARC or SiON or (silicon oxynitride) or "SiON") same ((heat treat\$3) or anneal\$3) same (oxygen or nitrogen or O2 or N2 or "O.sub.2" or "N.sub.2"))	3	<u>L15</u>
JPAB,EPAB,DWPI,TDBD	L13 and (ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3))	37	<u>L14</u>
	(SiN or (silicon nitride) or ("SiN.sub.X") or polysilicon) and ((dielectric or ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or		

JPAB,EPAB,DWPI,TDBD	(antireflect\$3) or (anti reflect\$3) or SiON or (silicon oxynitride) or "SiON" or SiONH or "SiONH" or "SiO.sub.2" or SiO2 or (silicon dioxide) or (silicon oxide)) and (anneal\$3 or (heat treat\$4)))	2030	<u>L13</u>
USPT,PGPB	L11 not L9	10	<u>L12</u>
USPT,PGPB	L7 and (ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3))	29	<u>L11</u>
USPT,PGPB	6268282.pn.	1	<u>L10</u>
USPT,PGPB	L8 and (ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3))	19	<u>L9</u>
USPT,PGPB	L7 and ((anneal\$3 or (heat treat\$4)) same (oxygen or nitrogen or O2 or N2 or "O.sub.2" or "N.sub.2"))	136	<u>L8</u>
USPT,PGPB	L6 and (SiN or (silicon nitride) or ("SiN.sub.X") or polysilicon) and ((dielectric or ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3) or (anti reflect\$3) or SiON or (silicon oxynitride) or "SiON" or SiONH or "SiONH" or "SiO.sub.2" or SiO2 or (silicon dioxide) or (silicon oxide)) same (anneal\$3 or (heat treat\$4)))	184	<u>L7</u>
USPT,PGPB	((427/569).icls. or (427/579).icls. or (427/162).icls. or (427/255.29).icls. or (427/255.37).icls. or (427/372.2).icls. or (427/397.7).icls. or (438/786).icls. or (438/787).icls. or (438/788).icls. or (438/791).icls. or ((438/792)!.ICLS.))	2981	<u>L6</u>
USPT,PGPB	(Taiwan Semiconductor) and ((ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3)) same (anneal or (heat treat\$4)))	2	<u>L5</u>
JPAB,EPAB,DWPI,TDBD	(Taiwan Semiconductor) and (ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3)) and (anneal or (heat treat\$4))	3	<u>L4</u>
USPT,PGPB	L2 and (anneal\$3 or (heat treat\$4))	4	<u>L3</u>
USPT,PGPB	L1 and (ARC or (anti-reflect\$3) or (AR (coat\$3 or film or layer)) or (antireflect\$3))	15	<u>L2</u>
USPT,PGPB	(Chiou.in. or Jang.in.) and (Taiwan semiconductor)	142	<u>L1</u>